Dirac Cones, Can Be Realized Generally in Bilayered Perovskites

XueJiao Chen,† 1, 2 Lei Liu,† 1 and DeZhen Shen1, 2

1 State Key Laboratory of Luminescence and Applications, Changchun Institute of Optics, Fine Mechanics and Physics, Chinese Academy of Sciences, No.3888 Dongnanhu Road, Changchun 130033, Peoples Republic of China
2 University of Chinese Academy of Sciences, Beijing 100049, Peoples Republic of China

(Dated: 2019-02-10)

We propose that the Dirac cone electronic states can be generally realized in those hexagonal perovskite bilayers sliced out directly from their cubic bulk phases. This is based on the simple analyses that the A-site atoms of these perovskites contribute neither valence nor conduction electrons and after the quasi-atom simplification their hexagonal bilayers indeed possess the honeycomb symmetry. Taking the CsPbBr$_3$ (111) bilayer as an example, with the density functional theory (DFT) calculations, we demonstrate their Dirac cones around the Fermi level and find the corresponding Fermi velocity, $\sim 2 \times 10^6$ m/s, can be almost twice as large as that of graphene. While under ambient conditions the solid ionic compounds normally do not conduct charge carriers very well, such high-velocity ballistic carrier transport in the new layered Dirac materials may revitalize the conventional perovskites and thereby bring new ultra-fast ionic electronics.

“Dirac Cone”, describing the gapless linear-dispersion of electronic bands, characterizes the superior ballistic massless charge-carrier transport of solids such as in graphene, or on the surfaces of topological insulators. Theoretically, the Dirac cones had been predicted in 1947 in graphene, whose honeycomb lattice of s-p bonding results in the conical band structure with the linearly dispersive valence and conduction bands touching each other at the Dirac points (K or K’). In fact, by energy-band theory and symmetry analysis, the normal Dirac cones as presented in graphene will generally appear in those materials, as long as they have the similarly honeycomb bonding style as graphene does. But, among hundreds of 2 dimensional (2D) materials examined by now, only graphene, silicene and germanene, ionic boron and others have been identified to be the normal Dirac materials. Obviously, these 2D Dirac materials are not that robust as graphene, since their atoms do not bond together as stable as they are in natural stable polymorphs. That means for the practical device applications under normal ambient conditions, these graphene analogues will be limited. In this letter, we propose for the first time that the Dirac cone states can be realized generally in cubic perovskites by slicing them directly into bilayers along hexagonal planes.

Theoretically, for oxide perovskites such as LaNiO$_3$, it was reported that its Ni atoms form naturally the buckled honeycombed lattice, and by adjusting the on-site interactions of Ni$^{3+}$ ions, the (111) LaNiO$_3$ bilayer can be possibly tuned into a Dirac half-semimetal material. And, for halide ones, based on theoretical analysis it was predicted that the cubic halide perovskites may undergo the transformation from semiconductor to dirac-semimetal with the hydrostatic pressure or uniform compression. Here, based on simple analyses of

![Energy band diagram](image)

FIG. 1. a The crystal structure of a cubic ABX$_3$ perovskite, where the green, gray, and brown balls represent the A cations, B cations, and the X anions, respectively; b the crystal structure of a cubic perovskite, viewed from its [111] direction; c the calculated electronic band structure of bulk CsPbBr$_3$, together with its total and site-decomposed DOS; d the effective crystal structure of a cubic ABX$_3$ perovskite, effectively seen by its low energy charge carriers; e the top view of the crystal structure of a BX$_6$ bilayer sliced out along the (111) plane of a cubic perovskite, which constructs the hexagonal honeycomb lattice with two equivalent BX$_6$ sublattices; and f the side view of the crystal structure of a hexagonal BX$_6$ bilayer, which indeed presents a buckled single quasi-atom (BX$_6$) layer.

energy-band and lattice-symmetry, we reveal that such practically uncontrollable tunings of on-site interactions or uniform compression are totally not necessary to realize Dirac states in perovskites.

Perovskites have the well-known ABX$_3$ lattice structure, as shown in Fig. 1, where the 6-fold coordinated B cation and its surrounded X anions form the BX$_6$ octahedron, the BX$_6$ octahedra share their X corners forming the 3D skeleton, and the A cations occupy every hole among the 8 BX$_6$ octahedra. For a cubic ABX$_3$ lattice, if viewed from the [111] direction, it presents natively the
hexagonal symmetry as shown in Fig. 1b. While the A cations stay isolated from the BX$_6$ skeleton, their electronic states normally do not participate in forming the low-energy bands dispersing near the Fermi level. For a selected halide perovskite (CsPbBr$_3$), Fig. 1c plots its gapped electronic band structure calculated with DFT, together with the total and site-decomposed density of states (DOS). That demonstrates clearly that the electronic orbitals the A cations stay a few electronvolts away from the valence band maximum (VBM) and the conduction band minimum (CBM) and thus play no role in deciding the low-energy electronic behaviors of a perovskite. Therefore, for those low energy charge carriers, whether electrons or holes, propagating in a perovskite crystal, the effective lattice they see would be without A cations as shown in Fig. 1d. For such a cubic lattice, if sliced out along the (111) plane, two BX$_6$ layers construct naturally the hexagonal honeycomb lattice with two equivalent BX$_6$ sublattices similar as graphene as shown in Fig. 1e. If considering the BX$_6$ octahedron as a quasi-atom, such a BX$_6$ bilayer transforms into a buckled single quasi-atom layer with structure exactly like silicene as shown in Fig. 1f.

Consequently, a hexagonal perovskite bilayer will present naturally the Dirac-cone electronic states as graphene at its Dirac points of K and K’. This is a corollary based on the honeycomb symmetry of BX$_6$ sublattices and the s- and p-binding characters of BX$_6$ octahedra. As a verification example, the hexagonal CsPbBr$_3$ bilayer was selected to calculate its electronic band structures near the Fermi level. Here, the DFT calculations were performed within Perdew-Burke-Ernzerhof (PBE) generalized gradient approximation and the projected augmented wave (PAW) method as implemented by the Vienna ab initio simulation package (VASP). The cutoff energy for the plane-wave basis set is 300 eV and the Brillouin zone is sampled with the Monkhorst-Pack mesh of $6 \times 6 \times 6$ for bulk and $6 \times 6 \times 1$ for bilayer CsPbBr$_3$. The lattice parameter of bulk CsPbBr$_3$ is set to its experimental value $a_0 = 5.874$ Å.

As expected, as shown in Fig. 2, its top valence and bottom conduction bands disperse linearly and touch each other at K and K’ points. Their orbital-decomposed DOS reveals clearly the s- and p-orbital nature of both bands around the Dirac points. And that is evidenced further by the insets of Fig. 2 which plot the isosurfaces of VBM and CBM partial charge densities. By fitting these two bands at $k = K + q$ to the expression $v_F \approx E(q)/|q|$, the Fermi velocity is estimated to be $v_F \approx 2 \times 10^6$ m/s. That means charge carriers may travel faster in this halide perovskite bilayer than in graphene ($v_F \approx 1 \times 10^6$ m/s).

In conclusion, we predict a new family of Dirac materials, i.e. hexagonal perovskite bilayers. Distinct to the previous graphene analogues identified so far, these Dirac materials are sliced out directly from the bulk perovskites, and possess the inborn stable 3D bonding structures. That makes them robust against the environmental disturbance in practical device applications. Moreover, unlike graphene from the covalent graphite, these perovskite Dirac bilayers actually originate from the ionic bulk materials. While in normal ionic crystals charge carriers usually cannot travel as fast as they do in conventional covalent semiconductors like Si, Ge, or GaAs, the coming of these Dirac perovskites indeed enables ionic solids to compete with the conventional covalent semiconductors in making ultra-fast electronic or optoelectronic devices.

ACKNOWLEDGMENTS

L. L. acknowledges the support from the National Science Fund for Distinguished Young Scholars of China (No. 61525404).


A. K. Geim and K. S. Novoselov, Nat. Mater. 6, 183 (2007).


